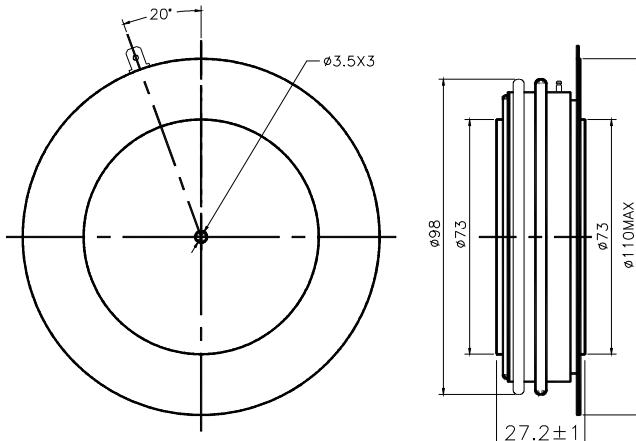


SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_J (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_{hs}=55^\circ C$	125			3973	A
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_{hs}=80^\circ C$	125			2929	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}$ tp=10ms $V_{DsM} \& V_{RsM} = V_{DRM} \& V_{RRM} + 100V$ respectively	125	400		1000	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			200	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			49.9	KA
I^2T	I^2T for fusing coordination	$V_R=0.6V_{RRM}$				12428	$A^2s * 10^3$
V_{TO}	Threshold voltage		125			0.82	V
r_T	On-state slop resistance					0.08	$m\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=5000A, F=40KN$	125			1.22	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			500	$V/\mu s$
di/dt	Critical rate of rise of on-state current	From 67% V_{DRM} to 2000A, Gate source 1.5A $t_r \leq 0.5\mu s$ Repetitive	125			400	$A/\mu s$
I_{rm}	Reverse recovery current	$I_{TM}=1500A, tp=1000\mu s,$ $di/dt=-20A/\mu s,$ $V_r=50V$	125			220	A
t_{rr}	Reverse recovery time					22	μs
Q_{rr}	Recovery charge					2420	μC
I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	40		300	mA
V_{GT}	Gate trigger voltage			0.8		3.0	V
I_H	Holding current			20		300	mA
V_{GD}	Non-trigger gate voltage	At 67% V_{DRM}	125			0.3	V
$R_{th(j-h)}$	Thermal resistance Junction to heatsink	At 180° sine' double side cooled Clamping force 40KN				0.011	$^\circ C / W$
F_m	Mounting force					35	KN
T_{Stg}	Stored temperature				-40	140	°C
W_t	Weight					1100	g
Outline	KT73cT						

Outline



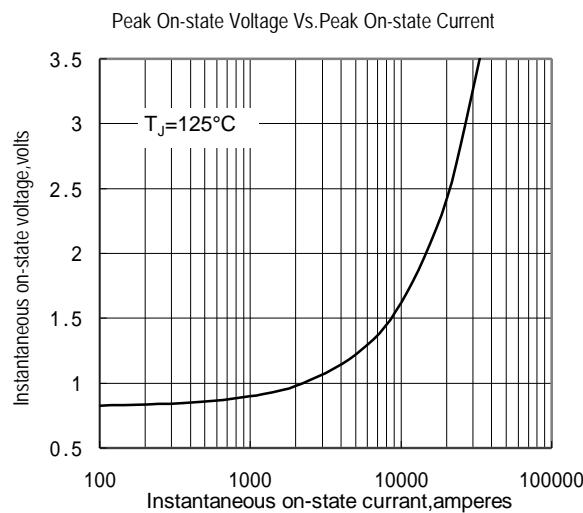


Fig.1

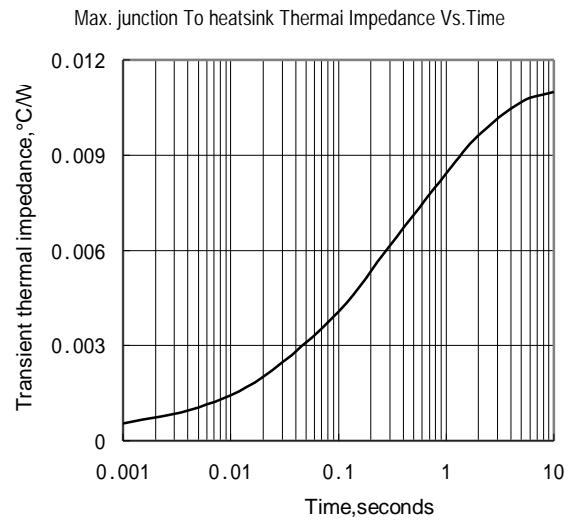


Fig.2

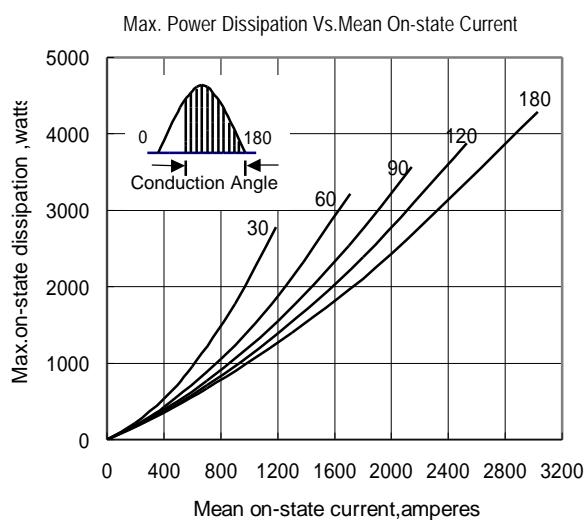


Fig.3

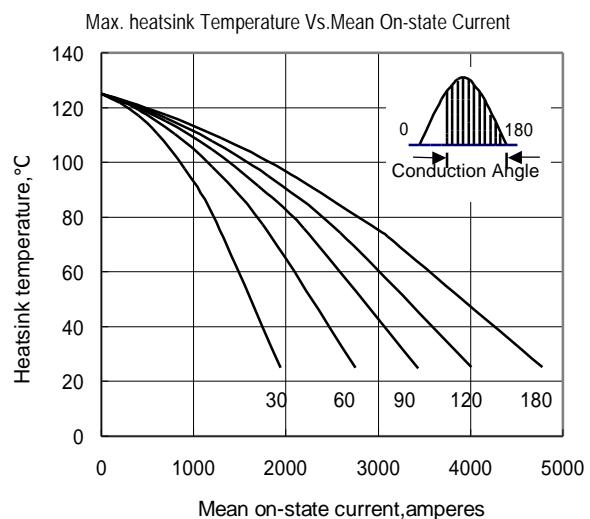


Fig.4

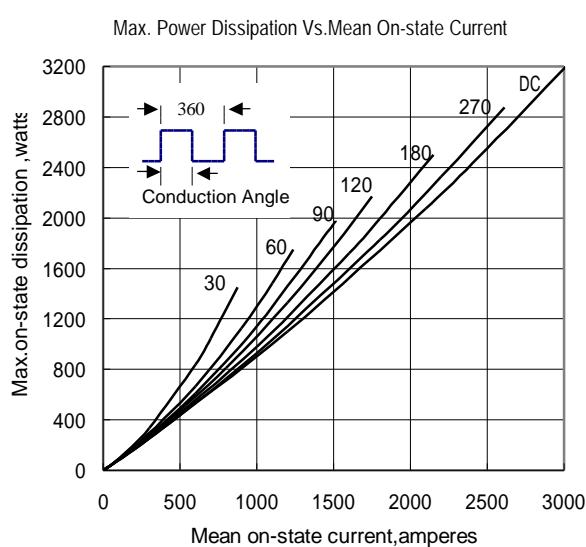


Fig.5

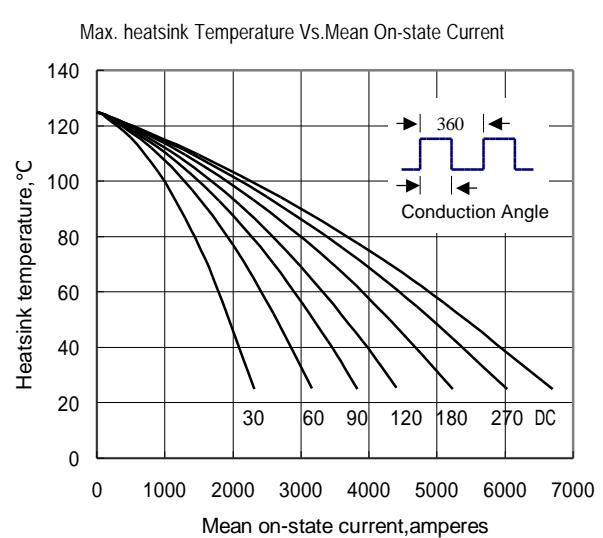


Fig.6

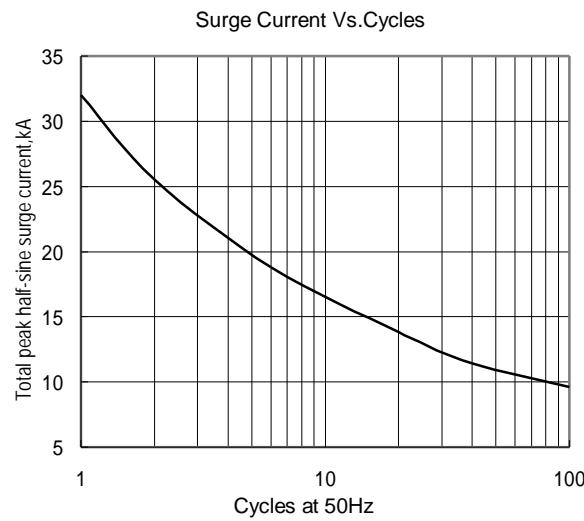


Fig.7

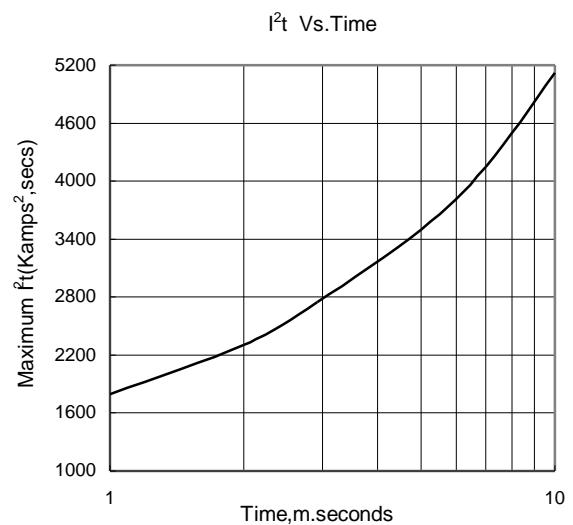


Fig.8

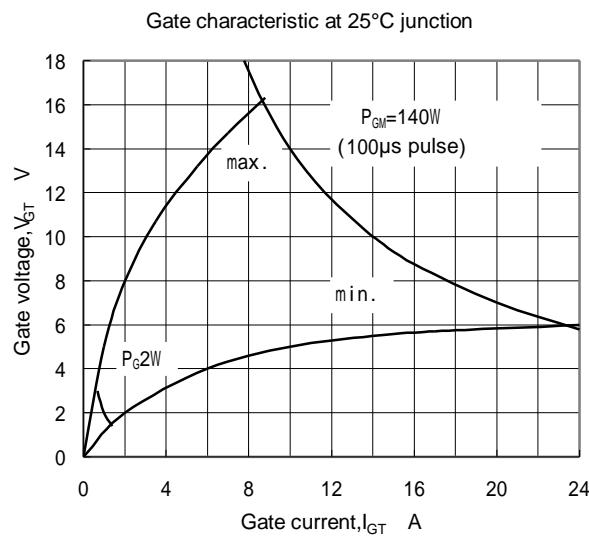


Fig.9

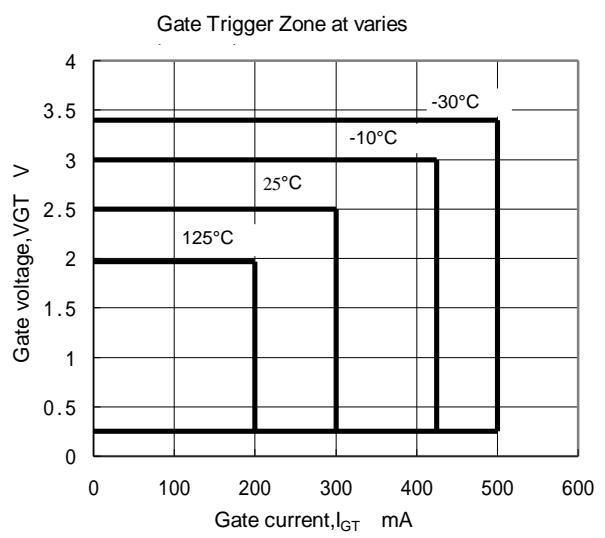


Fig.10